

LM13600 Dual Operational Transconductance Amplifiers with Linearizing Diodes and Buffers

General Description

The LM13600 series consists of two current controlled transconductance amplifiers each with differential inputs and a push-pull output. The two amplifiers share common supplies but otherwise operate independently. Linearizing diodes are provided at the inputs to reduce distortion and allow higher input levels. The result is a 10 dB signal-tonoise improvement referenced to 0.5 percent THD. Controlled impedance buffers which are especially designed to complement the dynamic range of the amplifiers are provided.

Features

- g_m adjustable over 6 decades
- Excellent g_m linearity

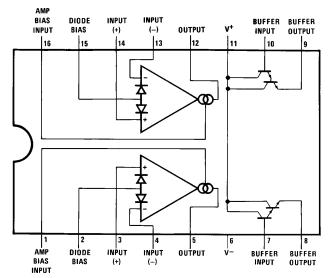
- Excellent matching between amplifiers
- Linearizing diodes
- Controlled impedance buffers
- High output signal-to-noise ratio

Applications

- Current-controlled amplifiers
- Current-controlled impedances
- Current-controlled filters
- Current-controlled oscillators
- Multiplexers
- Timers
- Sample and hold circuits

Connection Diagram

Dual-In-Line and Small Outline Packages



Top View

TL/H/7980-2

Order Number LM13600M, LM13600N or LM13600AN See NS Package Number M16A or N16A

Absolute Maximum Ratings

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (Note 1)

Buffer Output Current (Note 3)

 $\begin{array}{cccc} LM13600 & 36\ V_{DC}\ or\ \pm 18V \\ LM13600A & 44\ V_{DC}\ or\ \pm 22V \\ Power\ Dissipation\ (Note\ 2)\ T_A = 25^{\circ}C & 570\ mW \\ Differential\ Input\ Voltage & \pm 5V \\ Diode\ Bias\ Current\ (I_D) & 2\ mA \\ Amplifier\ Bias\ Current\ (I_{ABC}) & 2\ mA \\ Output\ Short\ Circuit\ Duration & Continuous \\ \end{array}$

 $\begin{array}{lll} \mbox{Operating Temperature Range} & \mbox{0°C to } + 70^{\rm °C} \\ \mbox{DC Input Voltage} & + \mbox{V}_{\rm S} \mbox{ to } - \mbox{V}_{\rm S} \\ \mbox{Storage Temperature Range} & -65^{\rm °C} \mbox{ to } + 150^{\rm °C} \\ \mbox{} \end{array}$

Soldering Information
Dual-In-Line Package

Soldering (10 seconds) 260°C

Small Outline Package
Vapor Phase (60 seconds) 215°C
Infrared (15 seconds) 220°C

See AN-450 "Surface Mounting Methods and Their Effect on Product Reliability" for other methods of soldering surface mount devices.

Electrical Characteristics (Note 4)

Parameter	Conditions	LM13600			LM13600A			Units
		Min	Тур	Max	Min	Тур	Max	Julia
Input Offset Voltage (V _{OS})	Over Specified Temperature Range		0.4	4		0.4	1 2	mV mV
	$I_{ABC} = 5 \mu A$		0.3	4		0.3	1	mV
V _{OS} Including Diodes	Diode Bias Current (I _D) = 500 μ A		0.5	5		0.5	2	mV
Input Offset Change	$5 \mu A \le I_{ABC} \le 500 \mu A$		0.1	3		0.1	1	mV
Input Offset Current			0.1	0.6		0.1	0.6	μΑ
Input Bias Current	Over Specified Temperature Range		0.4 1	5 8		0.4 1	5 7	μA μA
Forward Transconductance (g _m)	Over Specified Temperature Range	6700 5400	9600	13000	7700 4000	9600	12000	μmho μmho
g _m Tracking			0.3			0.3		dB
Peak Output Current	$ \begin{vmatrix} R_L = 0, I_{ABC} = 5 \; \mu A \\ R_L = 0, I_{ABC} = 500 \; \mu A \\ R_L = 0, Over Specified Temp Range \end{vmatrix} $	350 300	5 500	650	3 350 300	5 500	7 650	μΑ μΑ μΑ
Peak Output Voltage Positive Negative	$\begin{aligned} R_L &= \infty, 5 \ \mu A \leq I_{ABC} \leq 500 \ \mu A \\ R_L &= \infty, 5 \ \mu A \leq I_{ABC} \leq 500 \ \mu A \end{aligned}$	+ 12 - 12	+ 14.2 - 14.4		+12 -12	+ 14.2 - 14.4		V
Supply Current	$I_{ABC} = 500 \mu A$, Both Channels		2.6			2.6		mA
V _{OS} Sensitivity Positive Negative	Δ V _{OS} /ΔV+ Δ V _{OS} /ΔV-		20 20	150 150		20 20	150 150	μV/V μV/V
CMRR		80	110		80	110		dB
Common Mode Range		±12	± 13.5		±12	± 13.5		٧
Crosstalk	Referred to Input (Note 5) 20 Hz < f < 20 kHz		100			100		dB
Differential Input Current	$I_{ABC} = 0$, $I_{ABC} = \pm 4V$		0.02	100		0.02	10	nA
Leakage Current	I _{ABC} = 0 (Refer to Test Circuit)		0.2	100		0.2	5	nA

20 mA

Electrical Characteristics (Note 4) (Continued)

Parameter	Conditions	LM13600			LM13600A			Units
		Min	Тур	Max	Min	Тур	Max	Office
Input Resistance		10	26		10	26		kΩ
Open Loop Bandwidth			2			2		MHz
Slew Rate	Unity Gain Compensated		50			50		V/μs
Buffer Input Current	(Note 5), Except $I_{ABC} = 0 \mu A$		0.2	0.4		0.2	0.4	μΑ
Peak Buffer Output Voltage	(Note 5)	10			10			V

Note 1: For selections to a supply voltage above $\pm 22V$, contact factory.

Note 2: For operating at high temperatures, the device must be derated based on a 150°C maximum junction temperature and a thermal resistance of 175°C/W which applies for the device soldered in a printed circuit board, operating in still air.

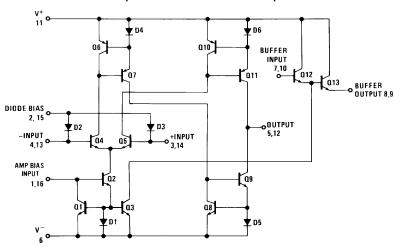
Note 3: Buffer output current should be limited so as to not exceed package dissipation.

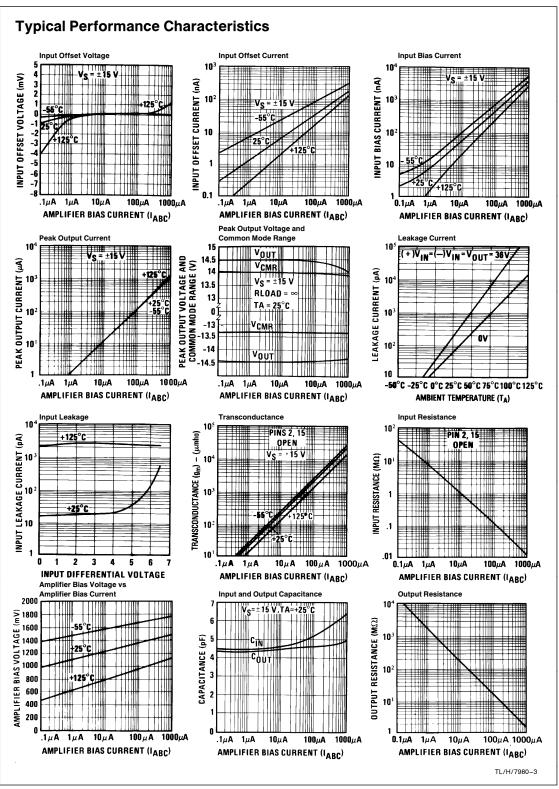
Note 4: These specifications apply for $V_S = \pm 15V$, $T_A = 25^{\circ}C$, amplifier bias current (I_{ABC}) = 500 μ A, pins 2 and 15 open unless otherwise specified. The inputs to the buffers are grounded and outputs are open.

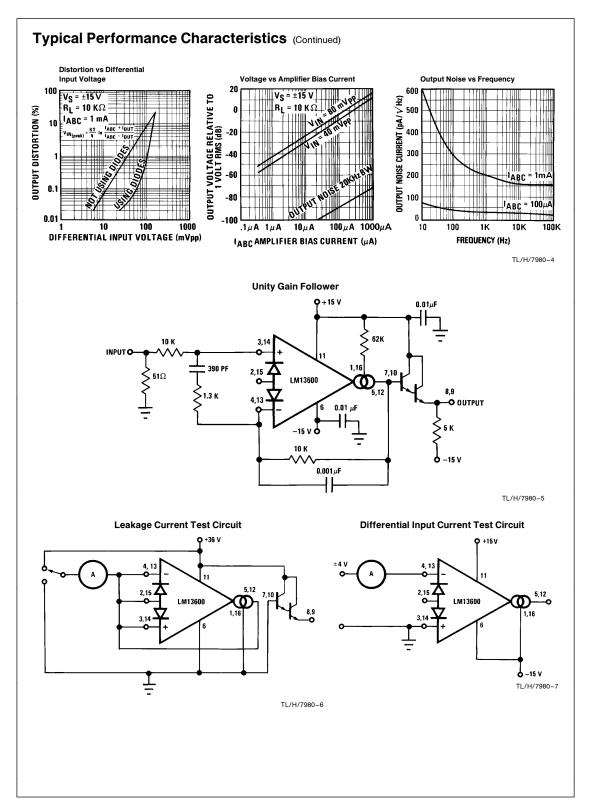
Note 5: These specifications apply for $V_S=\pm 15V$, $I_{ABC}=500~\mu A$, $R_{OUT}=5~k\Omega$ connected from the buffer output to $-V_S$ and the input of the buffer is connected to the transconductance amplifier output.

Schematic Diagram

One Operational Transconductance Amplifier







Circuit Description

The differential transistor pair Q_4 and Q_5 form a transconductance stage in that the ratio of their collector currents is defined by the differential input voltage according to the transfer function:

$$V_{IN} = \frac{kT}{a} \ln \frac{I_5}{I_4} \tag{1}$$

where V_{IN} is the differential input voltage, kT/q is approximately 26 mV at 25°C and I₅ and I₄ are the collector currents of transistors Q₅ and Q₄ respectively. With the exception of Q₃ and Q₁₃, all transistors and diodes are identical in size. Transistors Q₁ and Q₂ with Diode D₁ form a current mirror which forces the sum of currents I₄ and I₅ to equal I_{ABC};

$$I_4 + I_5 = I_{ABC}$$
 (2)

where $I_{\mbox{\scriptsize ABC}}$ is the amplifier bias current applied to the gain \min

For small differential input voltages the ratio of $\rm I_4$ and $\rm I_5$ approaches unity and the Taylor series of the In function can be approximated as:

$$\frac{kT}{q} \ln \frac{l_5}{l_4} \approx \frac{kT}{q} \frac{l_5 - l_4}{l_4}$$
 (3)

$$I_4 \approx I_5 \approx \frac{I_{ABC}}{2}$$

$$V_{IN} \left[\frac{I_{ABC} q}{2kT} \right] = I_5 - I_4 \tag{4}$$

Collector currents $\rm I_4$ and $\rm I_5$ are not very useful by themselves and it is necessary to subtract one current from the

other. The remaining transistors and diodes form three current mirrors that produce an output current equal to I_5 minus I_4 thus:

$$V_{IN} \left[\frac{I_{ABC} q}{2kT} \right] = I_{OUT}$$
 (5)

The term in brackets is then the transconductance of the amplifier and is proportional to I_{ABC}.

Linearizing Diodes

For differential voltages greater than a few millivolts, Equation 3 becomes less valid and the transconductance becomes increasingly nonlinear. Figure 1 demonstrates how the internal diodes can linearize the transfer function of the amplifier. For convenience assume the diodes are biased with current sources and the input signal is in the form of current I_S . Since the sum of I_A and I_S is I_{ABC} and the difference is I_{OUT} , currents I_A and I_S can be written as follows:

$$\mathsf{I_4} = \frac{\mathsf{I}_{ABC}}{2} - \frac{\mathsf{I}_{OUT}}{2}, \mathsf{I}_{5} = \frac{\mathsf{I}_{ABC}}{2} + \frac{\mathsf{I}_{OUT}}{2}$$

Since the diodes and the input transistors have identical geometries and are subject to similar voltages and temperatures, the following is true:

$$\begin{split} \frac{kT}{q} & \ln \frac{\frac{l_D}{2} + l_S}{\frac{l_D}{2} - l_S} = \frac{kT}{q} \ln \frac{\frac{l_{ABC}}{2} + \frac{l_{out}}{2}}{\frac{l_{ABC}}{2} - \frac{l_{out}}{2}} \\ & \therefore l_{out} = l_S \left(\frac{2l_{ABC}}{l_D} \right) \quad \text{for } |l_S| < \frac{l_D}{2} \end{split} \tag{6}$$

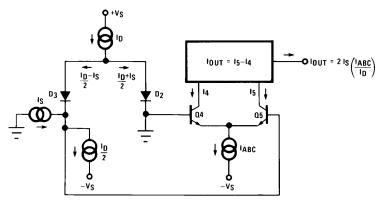


FIGURE 1. Linearizing Diodes

Linearizing Diodes (Continued)

Notice that in deriving Equation 6 no approximations have been made and there are no temperature-dependent terms. The limitations are that the signal current not exceed $I_{\rm D}/2$ and that the diodes be biased with currents. In practice, replacing the current sources with resistors will generate insignificant errors.

Controlled Impedance Buffers

The upper limit of transconductance is defined by the maximum value of $I_{\mbox{\footnotesize{ABC}}}$ (2 mA). The lowest value of $I_{\mbox{\footnotesize{ABC}}}$ for which the amplifier will function therefore determines the overall dynamic range. At very low values of IABC, a buffer which has very low input bias current is desirable. An FET follower satisfies the low input current requirement, but is somewhat non-linear for large voltage swing. The controlled impedance buffer is a Darlington which modifies its input bias current to suit the need. For low values of IABC, the buffer's input current is minimal. At higher levels of IABC, transistor Q3 biases up Q12 with a current proportional to I_{ABC} for fast slew rate. When I_{ABC} is changed, the DC level of the Darlington output buffer will shift. In audio applications where I_{ABC} is changed suddenly, this shift may produce an audible "pop". For these applications the LM13700 may produce superior results.

Applications—Voltage Controlled Amplifiers

Figure 2 shows how the linearizing diodes can be used in a voltage-controlled amplifier. To understand the input biasing, it is best to consider the 13 k Ω resistor as a current source and use a Thevenin equivalent circuit as shown in Figure 3. This circuit is similar to Figure 1 and operates the same. The potentiometer in Figure 2 is adjusted to minimize the effects of the control signal at the output.

For optimum signal-to-noise performance, I_{ABC} should be as large as possible as shown by the Output Voltage vs. Amplifier Bias Current graph. Larger amplitudes of input signal also improve the S/N ratio. The linearizing diodes help here by allowing larger input signals for the same output distortion as shown by the Distortion vs. Differential Input Voltage graph. S/N may be optimized by adjusting the magnitude of the input signal via $R_{\rm IN}$ (Figure 2) until the output distortion is below some desired level. The output voltage swing can then be set at any level by selecting $R_{\rm L}$.

Although the noise contribution of the linearizing diodes is negligible relative to the contribution of the amplifier's internal transistors, $I_{\rm D}$ should be as large as possible. This minimizes the dynamic junction resistance of the diodes $(r_{\rm e})$ and maximizes their linearizing action when balanced against $R_{\rm IN}.$ A value of 1 mA is recommended for $I_{\rm D}$ unless the specific application demands otherwise.

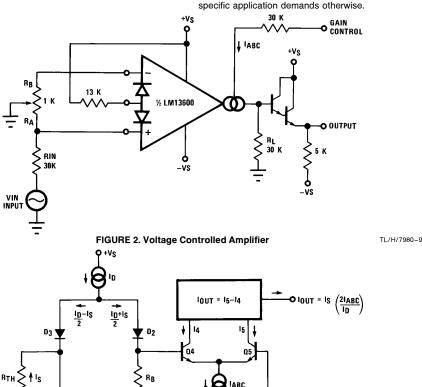


FIGURE 3. Equivalent VCA Input Circuit

RTH=RB

Stereo Volume Control

The circuit of Figure 4 uses the excellent matching of the two LM13600 amplifiers to provide a Stereo Volume Control with a typical channel-to-channel gain tracking of 0.3 dB. Rp is provided to minimize the output offset voltage and may be replaced with two 510Ω resistors in AC-coupled applications. For the component values given, amplifier gain is derived for Figure 2 as being:

If V_C is derived from a second signal source then the circuit becomes an amplitude modulator or two-quadrant multiplier as shown in *Figure 5*, where:

$$I_{O} = \frac{-2I_{S}}{I_{D}}(I_{ABC}) = \frac{-2I_{S}}{I_{D}}\frac{V_{IN2}}{R_{C}} - \frac{2I_{S}}{I_{D}}\frac{(V^{-} + 1.4V)}{R_{C}}$$

$$\frac{V_O}{V_{IN}} = 940 \times I_{ABC}$$

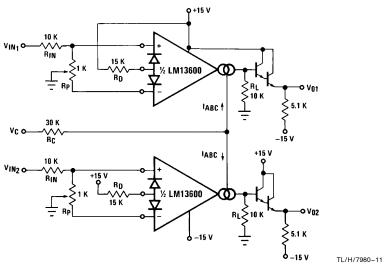


FIGURE 4. Stereo Volume Control

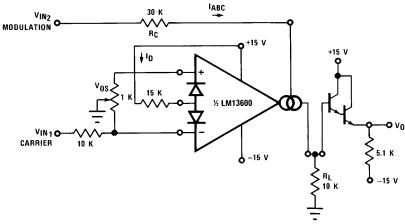


FIGURE 5. Amplitude Modulator

Stereo Volume Control (Continued)

The constant term in the above equation may be cancelled by feeding $I_S \times I_D R_C/2$ (V $^- + 1.4V$) into I_O . The circuit of Figure 6 adds R_M to provide this current, resulting in a four-quadrant multiplier where R_C is trimmed such that $V_O=0V$ for $V_{IN2}=0V$. R_M also serves as the load resistor for I_O .

Noting that the gain of the LM13600 amplifier of Figure 3 may be controlled by varying the linearizing diode current $\rm I_D$ as well as by varying $\rm I_{ABC}$, Figure 7 shows an AGC Amplifier using this approach. As V $_{O}$ reaches a high enough amplitude (3 V $_{BE}$) to turn on the Darlington transistors and the linearizing diodes, the increase in $\rm I_D$ reduces the amplifier gain so as to hold V $_{O}$ at that level.

Voltage Controlled Resistors

An Operational Transconductance Amplifier (OTA) may be used to implement a Voltage Controlled Resistor as shown

in Figure 8. A signal voltage applied at R_X generates a V_{IN} to the LM13600 which is then multiplied by the g_m of the amplifier to produce an output current, thus:

$$R_X = \frac{R \, + \, R_A}{g_m \, R_A}$$

where $g_m\approx 19.2\,I_{ABC}$ at 25°C. Note that the attenuation of V_O by R and R_A is necessary to maintain V_{IN} within the linear range of the LM13600 input.

Figure 9 shows a similar VCR where the linearizing diodes are added, essentially improving the noise performance of the resistor. A floating VCR is shown in Figure 10, where each "end" of the "resistor" may be at any voltage within the output voltage range of the LM13600.

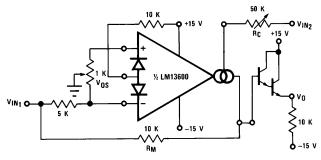


FIGURE 6. Four-Quadrant Multiplier

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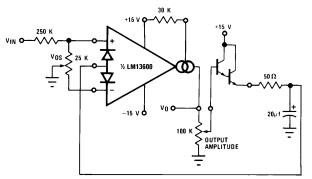


FIGURE 7. AGC Amplifier

TL/H/7980-14

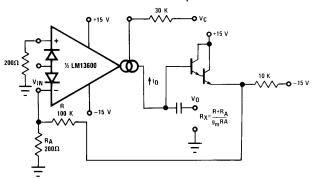


FIGURE 8. Voltage Controlled Resistor, Single-Ended

Voltage Controlled Filters

OTA's are extremely useful for implementing voltage controlled filters, with the LM13600 having the advantage that the required buffers are included on the I.C. The VC Lo-Pass Filter of Figure 11 performs as a unity-gain buffer amplifier at frequencies below cut-off, with the cut-off frequency being the point at which $X_{\rm C}/g_{\rm m}$ equals the closed-loop gain of (R/R_A). At frequencies above cut-off the circuit provides a single RC roll-off (6 dB per octave) of the input signal amplitude with a -3 dB point defined by the given equation,

where g_m is again 19.2 \times I_{ABC} at room temperature. *Figure 12* shows a VC High-Pass Filter which operates in much the same manner, providing a single RC roll-off below the defined cut-off frequency.

Additional amplifiers may be used to implement higher order filters as demonstrated by the two-pole Butterworth Lo-Pass Filter of *Figure 13* and the state variable filter of *Figure 14*. Due to the excellent $g_{\rm m}$ tracking of the two amplifiers and the varied bias of the buffer Darlingtons, these filters perform well over several decades of frequency.

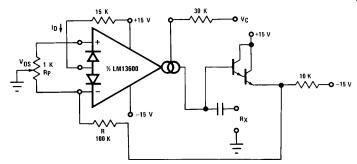


FIGURE 9. Voltage Controlled Resistor with Linearizing Diodes

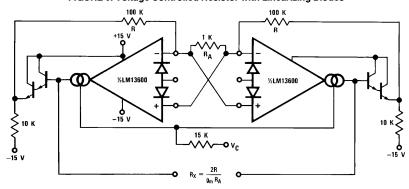


FIGURE 10. Floating Voltage Controlled Resistor

100 K
200Ω

NLM13600

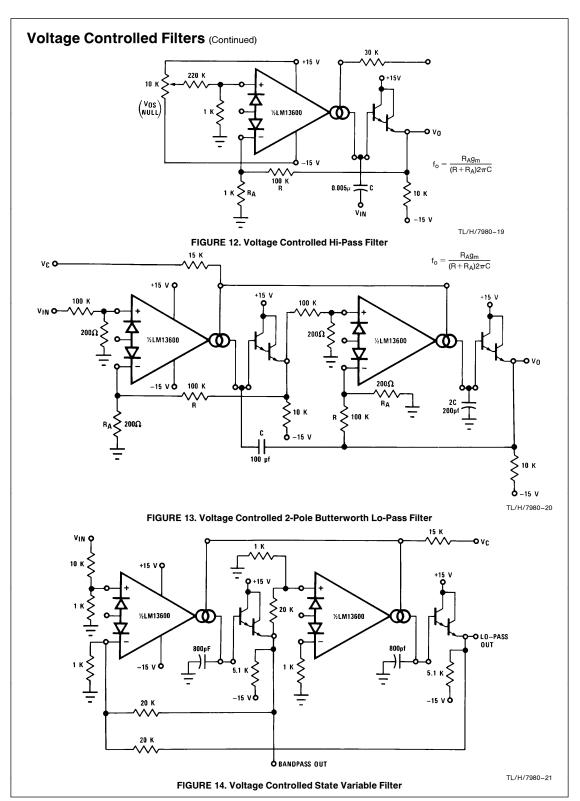
V0

fo= R_A9_m
(R+R_A)2πC

FIGURE 11. Voltage Controlled Low-Pass Filter

TL/H/7980-18

TL/H/7980-16



Voltage Controlled Oscillators

The classic Triangular/Square Wave VCO of Figure 15 is one of a variety of Voltage Controlled Oscillators which may be built utilizing the LM13600. With the component values shown, this oscillator provides signals from 200 kHz to below 2 Hz as $I_{\rm C}$ is varied from 1 mA to 10 nA. The output amplitudes are set by $I_{\rm A} \times R_{\rm A}.$ Note that the peak differential input voltage must be less than 5V to prevent zenering the inputs.

A few modifications to this circuit produce the ramp/pulse VCO of Figure 16. When $\rm V_{O2}$ is high, $\rm I_F$ is added to $\rm I_C$ to

increase amplifier A1's bias current and thus to increase the charging rate of capacitor C. When V_{O2} is low, I_F goes to zero and the capacitor discharge current is set by I_C .

The VC Lo-Pass Filter of *Figure 11* may be used to produce a high-quality sinusoidal VCO. The circuit of *Figure 16* employs two LM13600 packages, with three of the amplifiers configured as lo-pass filters and the fourth as a limiter/inverter. The circuit oscillates at the frequency at which the loop phase-shift is 360° or 180° for the inverter and 60° per filter stage. This VCO operates from 5 Hz to 50 kHz with less than 1% THD.

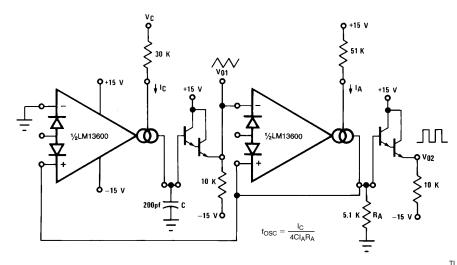
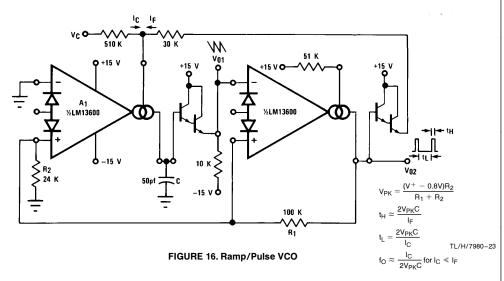


FIGURE 15. Triangular/Square-Wave VCO



Voltage Controlled Oscillators (Continued)

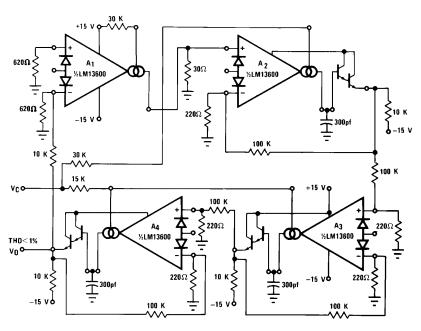


FIGURE 17. Sinusoidal VCO

TL/H/7980-24

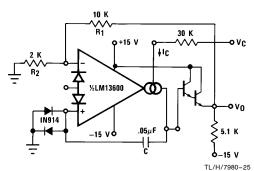


FIGURE 18. Single Amplifier VCO

Figure 18 shows how to build a VCO using one amplifier when the other amplifier is needed for another function.

Additional Applications

Figure 19 presents an interesting one-shot which draws no power supply current until it is triggered. A positive-going trigger pulse of at least 2V amplitude turns on the amplifier through $R_{\rm B}$ and pulls the non-inverting input high. The amplifier regenerates and latches its output high until capacitor C charges to the voltage level on the non-inverting input. The output then switches low, turning off the amplifier and discharging the capacitor. The capacitor discharge rate is increased by shorting the diode bias pin to the inverting input so than an additional discharge current flows through $D_{\rm I}$ when the amplifier output switches low. A special feature of this timer is that the other amplifier, when biased from $V_{\rm O}$, can perform another function and draw zero stand-by power as well.

The operation of the multiplexer of Figure 20 is very straightforward. When A1 is turned on it holds V_O equal to V_{IN1} and when A2 is supplied with bias current then it controls $V_O.\,C_C$ and R_C serve to stabilize the unity-gain configuration of amplifiers A1 and A2. The maximum clock rate is limited to about 200 kHz by the LM13600 slew rate into 150 pF when the $(V_{IN1}\text{-}V_{IN2})$ differential is at its maximum allowable value of 5V.

The Phase-Locked Loop of Figure 21 uses the four-quadrant multiplier of Figure 6 and the VCO of Figure 18 to produce a PLL with a $\pm 5\%$ hold-in range and an input sensitivity of about 300 mV.

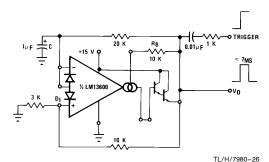


FIGURE 19. Zero Stand-By Power Timer

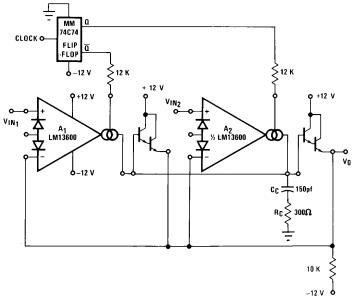


FIGURE 20. Multiplexer

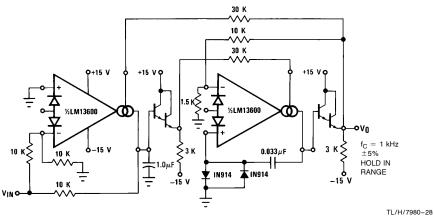


FIGURE 21. Phase Lock Loop

nase Lock Loop

The Schmitt Trigger of *Figure 22* uses the amplifier output current into R to set the hysteresis of the comparator; thus $V_H=2\times R\times I_B$. Varying I_B will produce a Schmitt Trigger with variable hysteresis.

Figure 23 shows a Tachometer or Frequency-to-Voltage converter. Whenever A1 is toggled by a positive-going input, an amount of charge equal to $(V_H - V_L)$ C_t is sourced into C_f and R_t . This once-per-cycle charge is then balanced by the current of V_O/R_t . The maximum f_{IN} is limited by the amount of time required to charge C_t from V_L to V_H with a current of I_B , where V_L and V_H represent the maximum low and maximum low and maximum low.

mum high output voltage swing of the LM13600. D1 is added to provide a discharge path for C_t when A1 switches low. The Peak Detector of Figure 24 uses A2 to turn on A1 whenever V_{IN} becomes more positive than V_{O} . A1 then charges storage capacitor C to hold V_{O} equal to $V_{\text{IN}}\text{PK}.$ One precaution to observe when using this circuit: the Darlington transistor used must be on the same side of the package as A2 since the A1 Darlington will be turned on and off with A1. Pulling the output of A2 low through D1 serves to turn off A1 so that V_{O} remains constant.

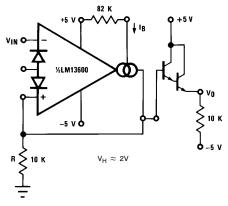


FIGURE 22. Schmitt Trigger

TL/H/7980-29

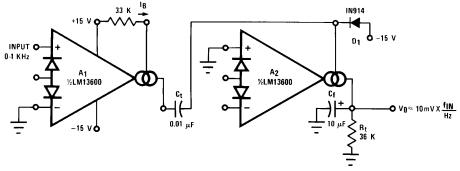


FIGURE 23. Tachometer

TL/H/7980-30

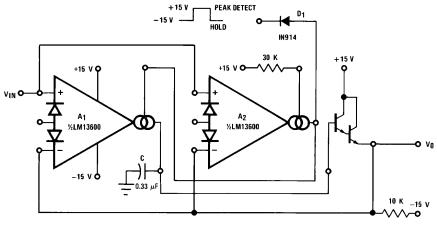


FIGURE 24. Peak Detector and Hold Circuit

The Sample-Hold circuit of *Figure 25* also requires that the Darlington buffer used be from the other (A2) half of the package and that the corresponding amplifier be biased on continuously. The Ramp-and-Hold of *Figure 26* sources I_B into capacitor C whenever the input to A1 is brought high, giving a ramp-rate of about 1 V/ms for the component values shown.

The true-RMS converter of *Figure 27* is essentially an automatic gain control amplifier which adjusts its gain such that the AC power at the output of amplifier A1 is constant. The output power of amplifier A1 is monitored by squaring amplifier A2 and the average compared to a reference voltage with amplifier A3. The output of A3 provides bias current to the diodes of A1 to attenuate the input signal. Because the output power of A1 is held constant, the RMS value is constant and the attentuation is directly proportional to the RMS value of the input voltage. The attenuation is also proportional to the diode bias current. Amplifier A4 adjusts the ratio of currents through the diodes to be equal and therefore the voltage at the output of A4 is proportional to the RMS value of the input voltage. The calibration potentiometer is set such that V_O reads directly in RMS volts.

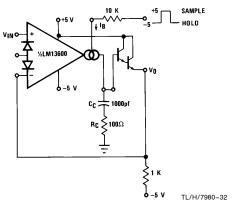


FIGURE 25. Sample-Hold Circuit

TL/H/7980-33

TL/H/7980-34

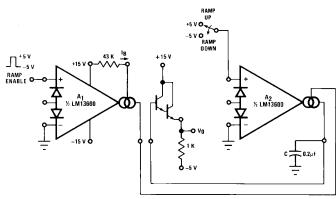


FIGURE 26. Ramp and Hold

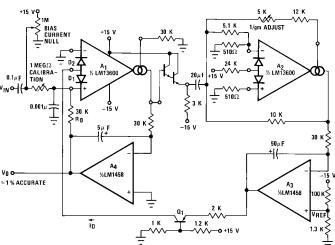


FIGURE 27. True RMS Converter

16

The circuit of Figure 28 is a voltage reference of variable temperature coefficient. The 100 $k\Omega$ potentiometer adjusts the output voltage which has a positive TC above 1.2V, zero TC at about 1.2V and negative TC below 1.2V. This is accomplished by balancing the TC of the A2 transfer function against the complementary TC of D1.

The log amplifier of Figure 29 responds to the ratio of currents through buffer transistors Q3 and Q4. Zero temperature dependence for V_{OUT} is ensured because the TC of the A2 transfer function is equal and opposite to the TC of the logging transistors Q3 and Q4.

The wide dynamic range of the LM13600 allows easy control of the output pulse width in the Pulse Width Modulator of *Figure 30*.

For generating I_{ABC} over a range of 4 to 6 decades of current, the system of *Figure 31* provides a logarithmic current out for a linear voltage in.

Since the closed-loop configuration ensures that the input to A2 is held equal to 0V, the output current of A1 is equal to $I_3 = -V_C/R_C$.

The differential voltage between Q1 and Q2 is attenuated by the R1, R2 network so that A1 may be assumed to be

operating within its linear range. From equation (5), the input voltage to A1 is:

$$V_{IN}1 = \frac{-2kTI_3}{qI_2} = \frac{2kTV_C}{qI_2R_C}$$

The voltage on the base of Q1 is then

$$V_B 1 = \frac{(R_1 + R_2) \, V_{IN} 1}{R_1}$$

The ratio of the Q1 and Q2 collector currents is defined by:

$$V_B 1 = \frac{kT}{q} ln \frac{l_{C2}}{l_{C1}} \approx \frac{kT}{q} ln \frac{l_{ABC}}{l_1}$$

Combining and solving for IABC yields:

$$I_{ABC} = I_1 exp \left[\frac{2(R_1 + R_2) V_C}{R_1 I_2 R_C} \right]$$

This logarithmic current can be used to bias the circuit of *Figure 4* provide a temperature independent stereo attenuation characteristic.

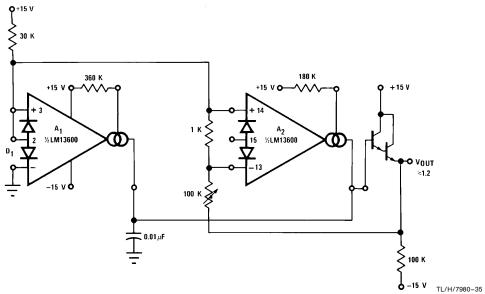
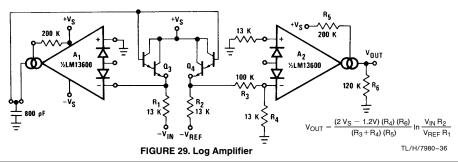


FIGURE 28. Delta VBE Reference



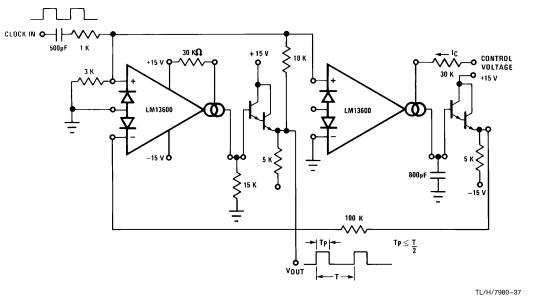


FIGURE 30. Pulse Width Modulator

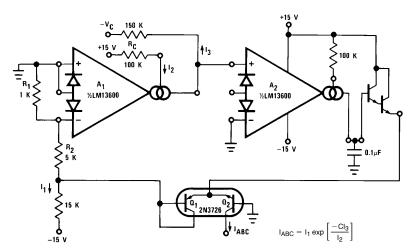
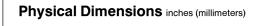
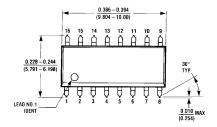
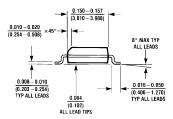
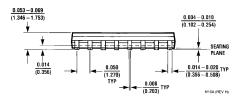


FIGURE 31. Logarithmic Current Source



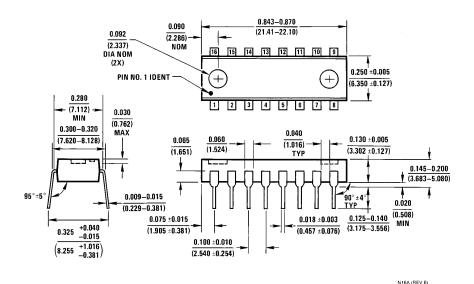






S.O. Package (M) Order Number LM13600M NS Package Number M16A

Physical Dimensions inches (millimeters) (Continued)



Molded Dual-In-Line Package (N) Order Number LM13600N or LM13600AN NS Package Number N16A

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